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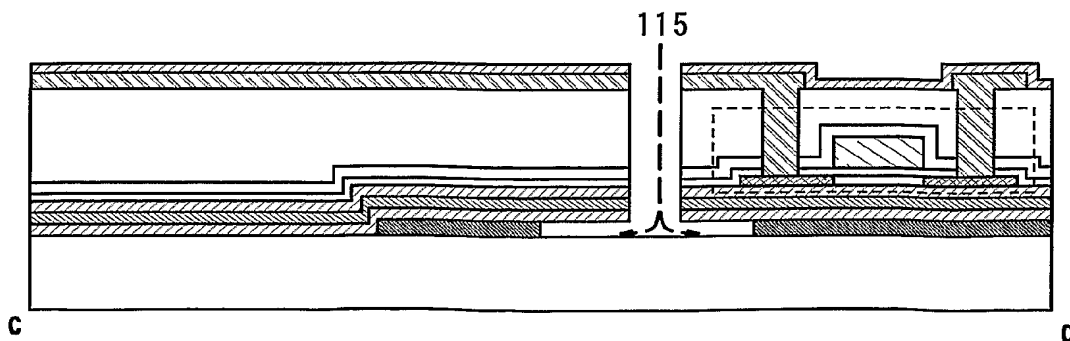
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(54) Title: METHOD FOR MANUFACTURING INTEGRATED CIRCUIT



(57) Abstract: A method for separating an integrated circuit formed by a thin film having a novel structure or a method for transferring the integrated circuit to another substrate, that is, so-called transposing method, has not been proposed. According to the present invention, in the case that an integrated circuit having a thin film having a novel structure formed over a substrate via a release layer is separated, the release layer is removed in the state that the thin film integrated circuit is fixated, the thin film integrated circuit is transposed to a supporting substrate having an adhesion surface, and the thin film integrated circuit is transposed

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